

TRIAC (ISOLATED TYPE) TO-240 PACKAGE

TSR70AA40/60

$$I_{T(RMS)} = 70A, V_{DRM} = 400/600V$$

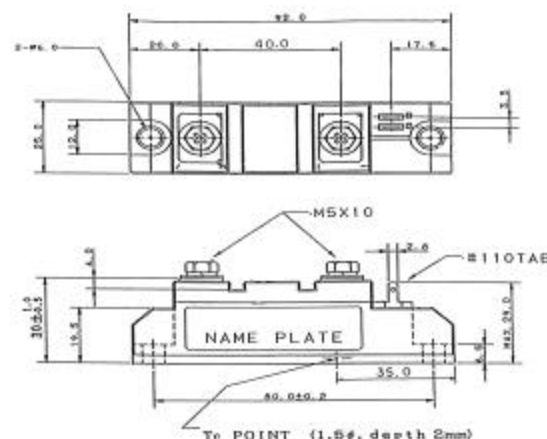
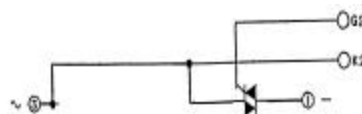
SanRex Triac **TSR70AA40/60** is designed for full-wave AC control applications. It can be used as an ON/OFF function or for phase control operations.

Features

- * Glass-passivated junctions Features
- * High Surge Current
- * UL registered E76102

Typical Applications

- * Heater Control
- * Motor Control
- * Lighting Control



< Maximum Ratings >

(Tj = 25°C Unless Otherwise Specified)

Symbol	Item	Ratings		Unit
		TSR70AA40	TSR70AA60	
V_{DRM}	Repetitive Peak Off-state Voltage	400	600	V
V_{DSM}	Non-Repetitive Peak Off-state Voltage	450	650	V

Symbol	Item		Conditions	Ratings	Unit
$I_{T(RMS)}$	R.M.S. On-state Current		$T_C = 101^{\circ}C$	70	A
I_{TSM}	Surge On-state Current		One cycle, 50Hz/60Hz, Peak, non-repetitive	900/1000	A
I^2t	I^2t (for fusing)		Value for one cycle surge current	4160	A ² s
P_{GM}	Peak Gate Power Dissipation			10	W
$P_{G(AV)}$	Average Gate Power Dissipation			1	W
I_{GM}	Peak Gate Current			3	A
V_{GM}	Peak Gate Voltage			10	V
di/dt	Critical Rate of Rise of On-state Current		$I_G=100mA$ $V_D=1/2V_{DRM}$ di/dt=1A/Fs	50	A/Fs
T_j	Operation Junction Temperature			-40 to +125	$^{\circ}C$
T_{stg}	Storage Temperature			-40 to +125	$^{\circ}C$
V_{ISO}	Isolation Breakdown Voltage		A.C. 1 minute	2500	V
	Mounting Torque	Mounting M5	Recommended Value 1.5 to 2.5 (15 to 25)	2.7(28)	N*m (kg * cm)
		Terminals M5	Recommended Value 1.5 to 2.5 (15 to 25)	2.7(28)	
	Mass		Typical Value	170	g

< Electrical Characteristics >

(Tj = 25°C Unless Otherwise Specified)

Symbol	Item		Conditions	Ratings			Unit
				Min.	Typ.	Max.	
I_{DRM}	Repetitive Peak Off-state Current		$T_J = 125^{\circ}\text{C}, V_D = V_{DRM}$			10	mA
V_{TM}	Peak On-State Voltage		$I_T = 100\text{A}$			1.35	V
I_{GT1}^{+}	QI	Gate Trigger Current	$V_D = 6\text{V}, I_T = 1\text{A}$			50	mA
I_{GT1}^{-}	QII		$V_D = 6\text{V}, I_T = 1\text{A}$			50	mA
I_{GT3}^{+}	QIV			-	-	-	mA
I_{GT3}^{-}	QIII		$V_D = 6\text{V}, I_T = 1\text{A}$			50	mA
V_{GT1}^{+}	QI	Gate Trigger Voltage	$V_D = 6\text{V}, I_T = 1\text{A}$			3	V
V_{GT1}^{-}	QII		$V_D = 6\text{V}, I_T = 1\text{A}$			3	V
V_{GT3}^{+}	QIV			-	-	-	V
V_{GT3}^{-}	QIII		$V_D = 6\text{V}, I_T = 1\text{A}$			3	V
V_{GD}	Non-Trigger Gate Voltage		$T_J = 125^{\circ}\text{C}, V_D = 1/2V_{DRM}$	0.2			V
dv/dt	Critical Rate of Rise of Off-State Voltage		$T_J = 125^{\circ}\text{C}, V_D = 2/3V_{DRM}, \text{exp. Wave}$	50			V/Fs
$(dv/dt)_c$	Critical Rate of Rise of Commutation Voltage		$T_J = 125^{\circ}\text{C}, V_D = 2/3V_{DRM} (di/dt)_c = 8\text{A/ms}$	6			V/Fs
I_H	Holding Current				50	100	mA
$R_{th(j-c)}$	Thermal Resistance		Junction to case			0.3	$^{\circ}\text{C/W}$